METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND PROGRAM

ABSTRACT

The present disclosure provides a technique for improving step coverage in film formation. According to one embodiment, there is provided a technique including: (a1) modifying at least a portion of the substrate by supplying a first modifying gas to the substrate; (a2) adsorbing a first element preferentially to a region that is not modified by the first modifying gas, by supplying a first process gas containing the first element to the substrate; (b1) modifying at least a portion of the substrate by supplying a second modifying gas to the substrate, wherein a decomposition temperature of the second modifying gas is different from a decomposition temperature of the first modifying gas; and (b2) adsorbing a second element preferentially to a region that is not modified by the second modifying gas, by supplying a second process gas containing the second element to the substrate.

Fig. 3